

FTB1366 TRANSISTOR (PNP)

FEATURES

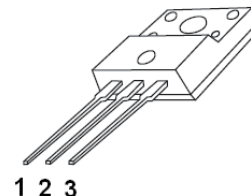
- Low $V_{CE(sat)}$: $V_{CE(sat)} = -1.0V(\text{Max.})(I_C/I_B = -2A/-0.2A)$
- Complementary to FTD2058

MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-60	V
V_{CEO}	Collector-Emitter Voltage	-60	V
V_{EBO}	Emitter-Base Voltage	-7	V
I_C	Collector Current -Continuous	-3	A
P_C	Collector power dissipation	2	W
T_J	Junction temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-55-150	$^\circ\text{C}$

TO-220F

1. BASE
2. COLLECTOR
3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = -1\text{mA}$, $I_E = 0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = -50\text{mA}$, $I_B = 0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = -1\text{mA}$, $I_C = 0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB} = -60\text{V}$, $I_E = 0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -7\text{V}$, $I_C = 0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE} = -5\text{V}$, $I_C = -0.5\text{A}$	60		200	
	$h_{FE(2)}$	$V_{CE} = -5\text{V}$, $I_C = -3\text{A}$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -2\text{A}$, $I_B = -0.2\text{A}$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE} = -5\text{V}$, $I_C = -0.5\text{A}$			-1	V
Transition frequency	f_T	$V_{CE} = -5\text{V}$, $I_C = -0.5\text{A}$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB} = -10\text{V}$, $I_E = 0$, $f = 1\text{MHz}$		150		pF
Fall time	t_f	$I_C = -2\text{A}$, $I_{B1} = -I_{B2} = -0.2\text{A}$		0.4		μs
Storage time	t_s	$V_{CC} = -30\text{V}$		1.7		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200

